## Quantum -m echanical wavepacket transport in quantum cascade laser structures

S.-C. Lee, <sup>1</sup> F. Ban $\pm$ , <sup>1</sup> M. Woerner, <sup>2</sup> and A. Wacker<sup>3</sup>,

<sup>1</sup>Institut fur Theoretische Physik, Technische Universitat Berlin, 10623 Berlin, Germany

<sup>2</sup>M ax-Born-Institut fur N ichtlineare O ptik und K urzzeitspektroskopie, 12489 Berlin, G erm any

<sup>3</sup>Fysiska Institutionen, Lunds Universitet, Box 118, 22100 Lund, Sweden

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W e present a viewpoint of the transport process in quantum cascade laser structures in which spatial transport of charge through the structure is a property of coherent quantum -m echanical wavefunctions. In contrast, scattering processes redistribute particles in energy and m om entum but do not directly cause spatial m otion of charge.

## I. INTRODUCTION

U nipolar quantum cascade (QC) laser devices<sup>1</sup> are intraband sem iconductor devices in which the transport processes and optical (intersubband) transitions which give rise to the lasing operation occur only in the conduction band of the sem iconductor structure. This marks a departure from previous interband sem iconductor lasers. Since the rst realization of a QC laser, there has been a proliferation of QC laser designs.<sup>2</sup> QC laser structures are composed of a complicated sequence of sem iconductor layers with di erent material compositions and thicknesses. This sequence is repeated tens or hundreds of times giving rise to a periodic structure in the device. Considering the complicated layer composition of these devices, the nature of the charge transport process through these structures is not in mediately apparent.

The original concept by Kazarinov and Suris<sup>3</sup> was based on coherent tunneling between neighboring wells. It was soon realized how ever that scattering plays a crucial role in establishing the nonequilibrium carrier distribution, in particular for the depopulation of the lower laser level. Thus alm ost all sim ulations of transport<sup>4,5,6,7</sup> in QC structures assume a sem iclassicalm odel, in which the transport occurs through scattering transitions between energy eigenstates (Wannier-Stark hopping<sup>8</sup>). In such an approach only diagonal elements of the density matrix (populations or distribution functions) in the W annier-Stark basis are used, and o diagonal elements are neglected (hence, the term sem iclassical). Ref. 5 brie y considered a more fully quantum -m echanical extension to this sem iclassical approach by also including o diagonal elements (coherences) of the density matrix in the calculation. This study concluded that quantum m echanical coherences were of lim ited in portance to the transport properties. However, coherent e ects were observed experim entally for the electron transfer from the injector to the upper laser level in QC structures.9,10 The importance of coherent e ects has also recently been stressed by Ref. 11, where a simplied calculation scheme is proposed.

The concept that scattering transitions propel the current through heterostructure systems con icts with the standard description of transport in bulk structures, where com plex B loch functions carry the current, while scattering redistributes the carriers in m om entum space but does not change their spatial positions.<sup>12</sup> W e will show that a similar description also holds in quantum cascade lasers where the current is carried by quantum – m echanical wavepackets, and the scattering only acts locally redistributing carriers in energy or m om entum .

#### II. THE MODEL

The quantum -m echanical transport theory we use here is based on nonequilibrium G reen's functions which allow for a consistent combination of scattering and coherent evolution. Q uantum -m echanical coherences are represented by o diagonal elements of the G  $\leq$  (E) correlation function, which is related to the density matrix  $k; k = dE G^{\leq}_{;k}$  (E)=2 i. The theory is formulated with basis states  $k(r;z) = (e^{ik} \frac{r}{-A})$  (z). Here (z) is the envelope function in the growth direction z. The wavevector k and the spatial coordinate r are two-dimensional vectors in the plane of each sem iconduc-

two-dimensional vectors in the plane of each sem iconductor layer (with norm alization area A), taking fully into account the three-dimensional nature of the structure. We divide the total H am iltonian as  $\hat{H} = \hat{H_o} + \hat{H_{scatt}}$ .

The free H am iltonian  $\hat{H}_{o}$  contains the kinetic energy and applied voltage, together with the electron-electron interaction in a mean eld approximation. It is diagonal in k, while  $\hat{H}_{scatt}$  describes scattering interactions k !  $k^{0}$ . Here we explicitly take into account acoustic phonon and longitudinal optical phonon, in purity, and interface roughness scattering processes.  $\hat{H}_{scatt}$  is treated perturbatively using self-energies in the self-consistent B om approximation. For example, for in purity scattering, the self-energy has the form

$$\binom{2}{0} \lim_{a,b} P_{a}(E) = \int_{0}^{A} h V^{im p}(q) V^{im p}_{0}(q) i G^{(a)}_{0}(q) i G^{(a)}_{0}(E)$$
 (1)

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where V<sup>in p</sup> represents the inpurity scattering potential.<sup>25</sup> In the following, we consider both the complete form of Eq. (1) with nondiagonal self-energies (ND), as well as approximations summarized in Table I. In each case, the system of equations for the G reen's functions and self-energies is solved self-consistently, which is an extensive numerical task.<sup>26</sup> This results

	hV	V	i	hV	V	i	hV	V	i	hV	V o oi
DG											
ND											
NDL											

TABLE I: Scattering potential matrix elements included in di erent self-energy models. ( ) indicates scattering potentialmatrix elements included (excluded) from the self-energy. The scattering potential V may represent in purity, interface roughness, orphonon scattering. The angle brackets represent an averaging over the in purity distribution for in purity scattering, the distribution of thickness uctuations for interface roughness scattering, and phonon modes for phonon scattering. DG indicates diagonal self-energies, while ND represents nondiagonal self-energies. NDL restricts the scattering matrix elements to local term sV for ND.

in the determination of the full correlation function  ${\rm G\,}^<$   $_{,\rm k}$  (E ), which describes the nonequilibrium state of the device.

Current densities are de ned as  $J = J_0 + J_{scatt} w$  ith

$$J_{o} = \frac{ieh[\hat{H}_{o};\hat{z}]i}{V^{\sim}} = \frac{2e}{\sim V} X \frac{Z}{k} \frac{dE}{2} [\hat{H}_{o};\hat{z}] G^{<}_{;k} (E)$$
(2)

and  $J_{scatt} = ieh[\hat{H}_{scatt}; 2]i=V^{-}$ . e < 0 is the electron charge and V is the sample volume. In Ref. 13 it was shown that  $J_{scatt}$  provides the hopping current due to scattering transitions between the states if one restricts to diagonal G reen functions and self-energies, i.e. neglects coherences between the states. Thus this part was referred to as scattering current, re ecting the (m is)conception that current ow occurs by a combination of both coherent evolution ( $J_o$ ) and relocation by scattering transitions. In the following we will show that  $J_{scatt}$  vanishes if coherences are properly taken into account, while the entire current is carried by  $J_o$ .

Basis states: The basis functions (z) can be chosen in di erent ways. In theory, the choice of basis states should not a ect the physical results. In practice, this choice can in uence the physical description in several ways: i) approximations are always necessary to perform the theoretical calculation or to facilitate the numerical computation, and the interplay between the chosen basis and the approximations may improve or reduce the validity of the approximations and hence a ect the physical result, ii) di erent choices of basis states can reveal different physical aspects of the problem. For instance, as we show in this paper, working with position eigenstates casts light on spatial aspects of the problem.

In our earlier work,<sup>13</sup> spatially-localized W annier states were used as an orthonormal set of (z), which can be constructed for the in nitely extended QC structure in a straightforward manner and generate a well-de ned periodic Ham iltonian. A second type of states are the W annier-Stark states, which are the eigenstates of  $\hat{H}_{o}$ . They can be easily obtained by diagonalizing  $\hat{H}_{o}$ 

in the basis of W annier states. (This procedure avoids the common use of an arti cial spatial con nement.) A third type of states constitutes the position eigenstate basis, using the eigenfunctions of the position operator  $\hat{z}$ . Again we start with the W annier basis, diagonalize  $\hat{z}$ , and transform  $\hat{H_o}$  into the new basis. In all bases we evaluate the scattering matrix elements directly for the respective basis functions.

Structures: The data presented below was obtained using two typicalexam ples: (A) a m idinfrared QC laser<sup>14</sup> and (B) a THzQC laser.<sup>15</sup> In the calculation we restrict the number of basis functions to 9 (5) per period for structures A (B).

#### III. VAN ISH ING OF J<sub>scatt</sub>

In Ref. 13, we neglected the o diagonal elements of the self-energies, i.e., only term s with  $= {}^{0}$  and  $= {}^{0}$  (diagonal self-energy, DG in Table I) were included in Eq. (1). In this restricted theory, we found  $J_{o}$  and  $J_{scatt}$  to be similar in magnitude. In contrast, using the more rigorous and complete formulation of the theory reported here, where all self-energy terms are included (nondiagonal self-energies, ND), we nd that  $J_{scatt} = 0$ . This result is basis invariant if the complete nondiagonal self-energies (ND) are used, as we checked this explicitly (numerically) for all three types of basis sets. Hence the total current density is given by  $J_{o}$ .

The same result has recently been analytically dem onstrated by Lake and Pandey.<sup>16</sup> In the position eigenstate basis, where the matrix z is diagonal, the expression (16) for  $J_{scatt}$  of R ef. 13 becomes

$$J_{\text{scatt}} = \frac{2e}{-V} \frac{X}{k} \frac{Z}{2} \frac{dE}{2} X \qquad Z \qquad G^{<}_{,k} \frac{adv}{k} + G^{\text{ret}}_{,k} \frac{<}{k} \frac{G^{adv}}{k} \frac{ret}{k} G^{<}_{,k} \frac{G^{adv}}{k} \frac{ret}{k} G^{<}_{,k}$$

Now the term in brackets corresponds to the right-hand side of the continuity equation as given in Eq. (57) of Ref. 17, which has to vanish. See also Section 2.4 of Ref. 18.

A second line of argument runs as follows: For microscopic scattering potentials which only depend on  $\hat{r}$  (but not on momentum  $\hat{p}$ ), the commutator  $[\hat{H}_{\text{scatt}};\hat{z}]$  vanishes and hence  $J_{\text{scatt}} = 0$  by its de nition. Thus  $J_{\text{scatt}} = 0$  holds for a wider class of scattering processes, including electron-electron scattering, than studied numerically here. These analytic arguments demonstrate that the previous observation of a nite  $J_{\text{scatt}}$  in Ref. 13 is an unphysical result caused by the DG -approximation in the self-energies for a nonlocal basis of W annier functions.

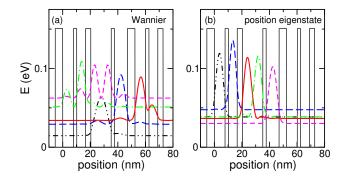


FIG.1: (Coloronline.) W avefunctions (modulus-squared) for Structure B. (a) W annier, (b) Position eigenstates.

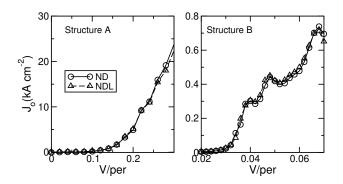


FIG.2: Current-voltage characteristic in position eigenstate basis with self-energy models ND and NDL.W e display  $J_0$ ;  $J_{scatt}$  0 in both cases.

## IV . SPATIALLY -LOCAL SCATTER ING IN $J_{\circ}$

A lthough  $J_{scatt}$  vanishes this does not imply that scattering processes are absent from the transport process. These processes do not appear explicitly in Eq. (2) but they act implicitly in determining  $G^{<}$  (E), and hence in driving the current  $J_o$ . We now investigate the role played by scattering processes in determining  $J_o$ . In particular, we seek to establish if each scattering event results in a spatial displacement of charge, or if a scattering process acts locally resulting in energy redistribution but with no accompanying spatial transport.

This issue can be conveniently addressed within the basis of position eigenstates. In contrast to the W annier wavefunctions [Fig. 1(a)], these position eigenfunctions are localized to within a single well layer in the structure [see Fig. 1(b)] and the scattering potential matrix elements h  $\frac{1}{5}$  j i are signi cantly smaller for  $\frac{6}{5}$  than for =. We therefore compare the e ect of excluding or including certain scattering potential terms in the self-energies, see Table I.

Fig. 2 shows that  $J_o^{N\,D\,L}$  and  $J_o^{N\,D}$  are almost identical for both samples. This indicates that the potential term s hV V i and hV V i constitute the main contribution to the self-energies in the calculation of  $J_o^{N\,D}$ , ourm ost rigorous form ulation of the current. These scattering terms involve only purely local (in space) transi-

tions, as V represents a transition matrix element between states with the same envelope function (z), i.e., localized to the same well. This implies that the scattering processes act only locally in space. They do not cause spatial displacement of charge, but act only to redistribute momentum k and energy.

A key point of our argument was the use of the position eigenstate basis which enabled us to demonstrate that the dom inant scattering processes in J<sub>o</sub> act locally and therefore do not contribute to the spatial transport of charge by  $J_{0}$ . This result is not evident if we work in another basis, e.g., W annier or W annier-Stark, where the wavefunctions are farm ore delocalized and o -diagonal m atrix elem ents V play a signi cant role. Nevertheless, physical mechanisms, such as the nature of transport, must be basis invariant. Indeed, as long as the full self-energies are taken into account, the expression for the currents  $J_{0}$  and  $J_{\text{scatt}}$  are invariant under basis transform ations. This dem onstrates that the same result is recovered even in the case of a delocalized basis, where the interplay of all types of matrix elements in Table I reproduces the locality of scattering transitions. In contrast, the neglect of certain m atrix elem ent com binations (such as the DG -approxim ation) generates spurious nonlocal scattering transition in a delocalized basis.

# V. TRANSPORT OF $J_{\rm o}$ BY COHERENT WAVE FUNCTIONS

As we have just seen, the scattering processes which contribute to  $J_o$  have a purely local e ect which does not spatially displace carriers. Hence, we conclude that the transport of charge by  $J_o$  through the structure must arise as a property of the quantum -m echanical wavefunction. We can obtain a more concrete visualization of this transport mechanism by resolving  $J_o$  in energy and space:

$$J_{o}(E;z) = \frac{e}{A} A^{K} Re \frac{a}{m(z)} (z) \frac{e(z)}{e^{Z}} G^{K}(E) ;$$
(3)

The lower panel of Fig. 3 show that the current  $J_{\circ}$  (E;z) ows at di erent energies in di erent spatial regions of the structures. To satisfy the equation of continuity, scattering interactions enable energy transitions which occur locally as discussed above (an example is depicted by the vertical arrow in the gure). Thus, scattering gives rise to a redistribution of electrons in energy but does not cause a spatial displacement or spatial transport of charge.<sup>27</sup>

Fig. 4 shows the corresponding result for sample A. Here the current density is restricted to a narrow energy range while crossing the thick barrier (around z = 2 nm) between the injector and the active region, thus providing the desired selective feeding of the upper laser level. This demonstrates how this representation allows for a detailed insight into the microscopic operation of the device.

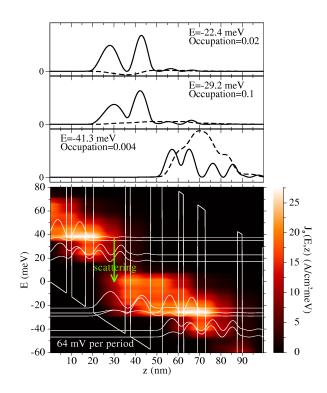


FIG.3: (C obr online.) Lower panel: Spatially and energetically resolved current from Eq. (3) for sample B.The wavefunctions depict some quasi-levels, which are eigenstates of  $\hat{H}_{o}$  at k = 0 renorm alized by the scattering interactions. Upper panels: P robability density  $j_{nk}(z)\hat{f}$  (black line) and current / Ref i  $_{nk} \hat{}_{nk}^{0}(z)$ =m (z)g (dashed line) for the complex wave functions  $_{nk}(z)$  for k = 0.n corresponds to the largest eigenvalue  $f_{n0}(E)$  for the respective values of E. These energies are chosen as local maxim a  $E_{max}$  of  $f_{n0}(E)$  with FW HM E ( 1 m eV) and the respective occupations have been approxim ated by ( =2)  $f_{n0}(E_{max}) E$ .

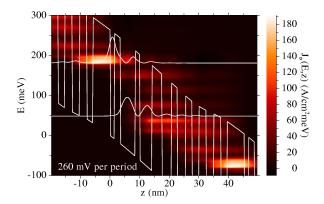


FIG. 4: (Color online.) Spatially and energetically resolved current from Eq. (3) for sample A. The quasi-levels, which are eigenstates of  $\hat{H_o}$  at k = 0 renorm alized by the scattering interactions are shown for the upper and lower laser state for com parison.

An especially intuitive form of Eq. (3) can be obtained by transforming into an (energy-dependent) basis of eigenstates of the hermitian matrix  $i=(2)G^{<}_{,k}(E)$  which has real eigenvalues  $f_{nk}(E)$ . While  $f_{nk}(E)$  exhibits sharp peaks in energy, the eigenstates  $_{nk}(z)$  exhibit only a weak energy dependence (not shown for brevity). Then we nd

$$J_{o}(E;z) = \frac{2e}{A} \sum_{nk}^{X} f_{nk}(E)Re \sum_{nk} (z) \frac{(i^{-})}{m} \frac{e_{nk}(z)}{e^{-}} :$$
(4)

Thus, the energy-resolved current is carried by wave functions  $_{nk}$  (z) with occupation densities  $f_{nk}$  (E) (the factor 2 is due to spin). This is analogous to the B loch functions and their occupation in standard bulk transport. The upper panels of Fig. 3 show that these current carrying states  $_{nk}$  (z) extend over a range of one period. This length scale gives a m easure of the coherence length, i.e., the distance over which charge is transported by a single coherent wave packet. The peaks in density  $j_{nk}(z) \hat{f}$  are localized in the wells as charge tends to accum ulate in the low-potential regions. The currents carried by the wave functions nk (z) are more evenly distributed which reects the ability of the wave packets to transport charge across the structure. Note the nonvanishing divergence of current density which re ects the local balance of scattering processes. Thus, these complex wave functions nk (z) can be viewed as generalized states for a nonequilibrium system, where the drive by bias and scattering processes com pensate.

The currents associated with these wavepackets can di er signi cantly: The state at -29.2 m eV (corresponding to the upper laser level) has only a sm all current, but a high occupation. In contrast, the state at E = 41.3m eV (lower laser level) exhibits a strong current to the right, e ectively moving electrons away from the lasing transition which occurs vertically between these states. There are also states exhibiting local current ow to the left, e.g., at 22.4 m eV. Such considerations may provide new tools for the optim ization and design of new laser structures.

The complex states  $_{nk}(z)$  are of particular importance at level crossings. This is demonstrated in Fig. 5 for a simple superlattice at the resonance between the ground state and the rst excited state of the neighboring well. Fig. 5 (a) depicts the W annier-Stark states, which are spread over both wells. The rst two eigenvalues  $f_{n0}$  (E) (for k = 0) exhibit a clear peak at the level energies [see Fig. 5 (b)] and the corresponding states, carry particles to the right [state 1, Fig. 5 (c)] and to the left [state 2, Fig. 5 (d)]. How ever, the occupation of the state 1 is about two orders of magnitude larger thus providing a strong current ux over the barrier.

Our viewpoint of current-carrying coherent wavefunctions di ers essentially from the conception that scattering transitions propel the current. This manifests itself in two ways: (i) In a scattering transition picture,

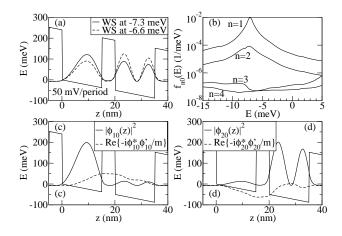


FIG. 5: States for the superlattice of R ef. 19. (a) Doublet of W annier-Stark states. (b) Eigenvalues  $f_{nk}$  (E) of  $i=(2)G^{<}_{,k}$  (E) for k = 0. (c,d) Corresponding eigenfunctions  $_{nk}$  (z) at E = 7m eV for the two largest eigenvalues,  $f_{1k}$  and  $f_{2k}$ , respectively.

the current would stop in m ediately once the scattering processes stop (H  $_{scatt}$  drops to zero). However, the occupation of current-carrying wave-functions only changes on the scale of the scattering time, thus the current ow will continue on this time scale. (ii) The current is sensitive to quantum m echanical phases. E.g., phase conjugation would reverse the direction of  $J_o$ , while scattering rates would be una ected.

#### VI. RELATION TO WANNIER-STARK HOPPING MODEL

In the W annier-Stark hopping model, the current is carried by scattering transitions between W annier-Stark states and depends only on scattering rates and the populations of these states. The coherences, i.e., o diagonal elements k; k (diagonal in k in contrast to scattering transition am plitudes  $k; k^{\circ}$ ) of the density matrix, play no role in thism odel and are neglected. There are two peculiarities in this picture: (i) The W annier-Stark hopping picture of transport through scattering transitions and our picture of transport by coherent wavepackets each provide the entire current and yet o er such con icting views of the transport mechanism. (ii) If we examine Eq. (2) expressed in the W annier-Stark basis, we see that a diagonal density matrix results in zero total current.28 Thus, coherences are central to the transport process, even in the W annier-Stark basis, see also Ref. 20. This con icts with the common W annier-Stark hopping picture. How do we reconcile these contradictions? The answer is that the W annier-Stark hopping m odel is derived from Eq. (2) by expressing, in a low-order approximation, the o diagonal elements of the density m atrix in terms of the diagonal elements.<sup>21,22,23</sup> Under conditions where such an approximation is applicable the W annier-Stark hopping m odel gives the same results as a full quantum transport m odel (see, e.g., Ref. 23 for superlattices), but it should be remembered that the W annier-Stark hopping m odel uses populations which are in actual fact an approximation for the coherences.

Following the concepts of standard quantum optics, one is tempted to assume that coherences are created by the electric eld and destroyed by scattering. However, the opposite is true in the quantum treatment of transport within the basis of W annier-Stark states, which are eigenstates of  $\hat{H}_{\circ}$  including the electrostatic potential. Here coherences are induced by the scattering processes via the non-diagonal self-energies, which are crucial in a consistent quantum treatment.

## VII. SUMMARY

We have shown that the entire current through QC structures is carried only by complex, quantum mechanical wavefunctions as shown, e.g., in the upper panel of Fig. 3. This conclusion follows from two main results: (i) The scattering current J<sub>scatt</sub> vanishes, which directly follows from  $[\hat{H}_{scatt}; \hat{z}] = 0$ , if the scattering potentials couple to the spatial coordinate of electron states. (ii) In the position basis, only the diagonal scattering m atrix elements V are signi cant in determ ining the current  $J_{\alpha}$ , and hence the entire current. Such matrix elem ents do not induce spatial translation of the electron state within the scattering transition. Thus, the principal scattering events which transferm om entum and/ordissipate energy in the transport process in quantum cascade structures occur only through spatially-local transitions which do not give rise to propagation of charge.

The locality of scattering transitions contrasts with the simple picture of electrons hopping between energy eigenstates due to scattering events, which is a common description in heterostructure system s. On the other hand, our point of view is analogous to bulk transport, where the scattering term in Boltzm ann's equation is local in space, and the entire current is carried by B loch states.

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E lectronic address: Andreas W acker@ fysik.lu.se

<sup>&</sup>lt;sup>1</sup> J.Faist, F.Capasso, D.L.Sivco, C.Sirtori, A.L.Hutchinson, and A.Y.Cho, Science 264, 553 (1994).

<sup>&</sup>lt;sup>2</sup> C. Gm achl, F. Capasso, D. L. Sivco, and A. Y. Cho, Rep. Prog. Phys. 64, 1533 (2001).

<sup>&</sup>lt;sup>3</sup> R.F.Kazarinov and R.A.Suris, Sov.Phys.Sem icond.6,

120 (1972), Fiz. Tekh. Poluprov. 6, 148 (1972)].

- <sup>4</sup> K.Donovan, P.Harrison, and R.W. Kelsall, J.Appl.Phys. 89, 3084 (2001).
- <sup>5</sup> R.C. Iotti and F. Rossi, Phys. Rev. Lett. 87, 146603 (2001).
- <sup>6</sup> O.Bonno, J.Thobel, and F.Dessenne, J.Appl.Phys.97, 043702 (2005).
- <sup>7</sup> A.M. ircetic, D.Indjin, Z.Ikonic, P.Hanrison, V.M. ilanovic, and R.W. Kelsall, J.Appl. Phys. 97, 084506 (2005).
- $^{8}$  R.Tsu and G.Dohler, Phys.Rev.B 12, 680 (1975).
- <sup>9</sup> F. Eickem eyer, K. Reim ann, M. Woemer, T. Elsaesser, S. Barbieri, C. Sirtori, G. Strasser, T. Muller, R. Bratschitsch, and K. Unterrainer, Phys. Rev. Lett. 89, 047402 (2002).
- <sup>10</sup> M .W oemer, K .R eim ann, and T .E lsaesser, J.P hys.: C ondens.M atter 16, R 25 (2004).
- $^{11}$  H.Callebaut and Q.Hu,J.Appl.Phys.98,104505 (2005).
- <sup>12</sup> N.W. A shcroft and N.D.M erm in, Solid State Physics (Saunders College, Philadelphia, 1976).
- $^{13}$  S.C.Lee and A.W acker, Phys.Rev.B 66, 245314 (2002).
- <sup>14</sup> C. Sirtori, P. Knuck, S. Barbieri, P. Collot, J. Nagle, M. Beck, J. Faist, and U. Oesterle, Appl. Phys. Lett. 73, 3486 (1998).
- <sup>15</sup> B.S.W illiam s, H.Callebaut, S.Kum ar, Q.Hu, and J.L. Reno, Appl.Phys.Lett. 82, 1015 (2003).
- <sup>16</sup> R.K.Lake and R.R.Pandey, Nonequilibrium Green functions in electronic device modeling, preprint.
- <sup>17</sup> R. Lake, G. K lim eck, R. C. Bowen, and D. Jovanovic, J. Appl. Phys. 81, 7845 (1997).
- <sup>18</sup> G.D.Mahan, Phys. Rep. 145, 251 (1987).
- <sup>19</sup> S. Zeuner, B. J. Keay, S. J. Allen, K. D. Maranowski,

A.C.Gossard, U.Bhattacharya, and M.J.W.Rodwell, Phys.Rev.B 53, 1717 (1996).

- <sup>20</sup> R.C. Iotti, E.Ciancio, and F.Rossi, Phys. Rev. B 72, 125347 (2005).
- <sup>21</sup> D. Calecki, J. F. Palmier, and A. Chomette, J. Phys. C: Solid State Phys. 17, 5017 (1984).
- <sup>22</sup> Y.Lyanda-Geller and J.P.Leburton, Sem icond.Sci.Technol.10, 1463 (1995).
- <sup>23</sup> A.W acker, Phys. Rep. 357, 1 (2002).
- <sup>24</sup> F. Banit, S.-C. Lee, A. Knorr, and A. Wacker, Appl. Phys. Lett. 86, 41108 (2005).
- <sup>25</sup> For <sup>ret</sup> and self-energies for other scattering processes, see Ref. 13. Im purity scattering is treated m icroscopically as in Ref. 24. W e only treat electron-electron scattering in a m ean eld approximation, but it has been shown that for intersubband transport, electron-im purity scattering usually dom inates over electron-electron scattering, see C allebaut, K um ar, W illiam s, H u, and Reno, Appl. Phys. Lett. 84, 645 (2004).
- <sup>26</sup> W e use an iterative scheme based on the Broyden method, V.Eyert, J.Comp.Physics 124, 271 (1996).
- $^{27}$  As a further check on the calculation, current continuity requires that the integration of Eq. (3) over energy should result in  $J_{\rm o}\left(z\right)=\int dE \; J_{\rm o}\left(z;E\right)=$  a constant. Numerically, we observe a spatial variation due to the limited number of basis states used in the calculation. Increasing the number of basis states to 8 W annier states per period (also used in Fig. 3) reduces this variation to < 10\%.
- <sup>28</sup> This can also be seen in Eq. (4) of Ref. 21 or Eq. (9) of Ref. 22.